

FIG. 1
(PRIOR ART)

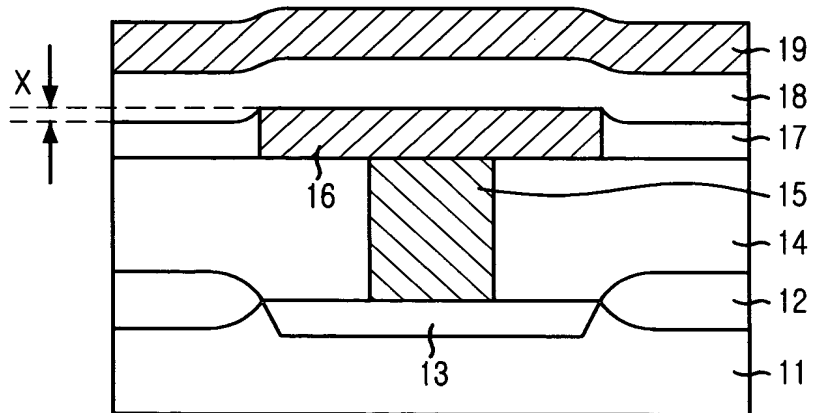


FIG. 2A

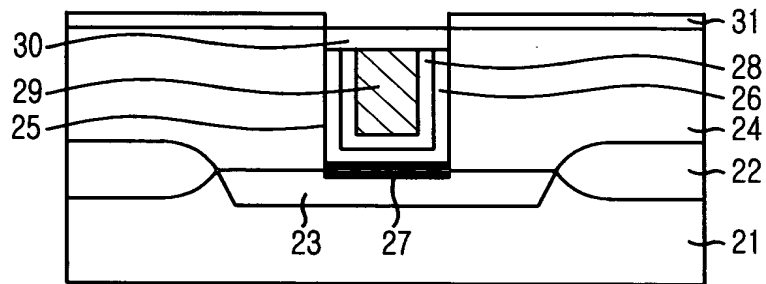


FIG. 2B

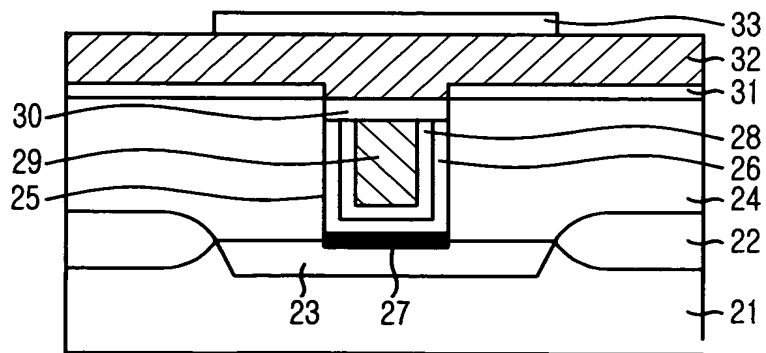


FIG. 2C

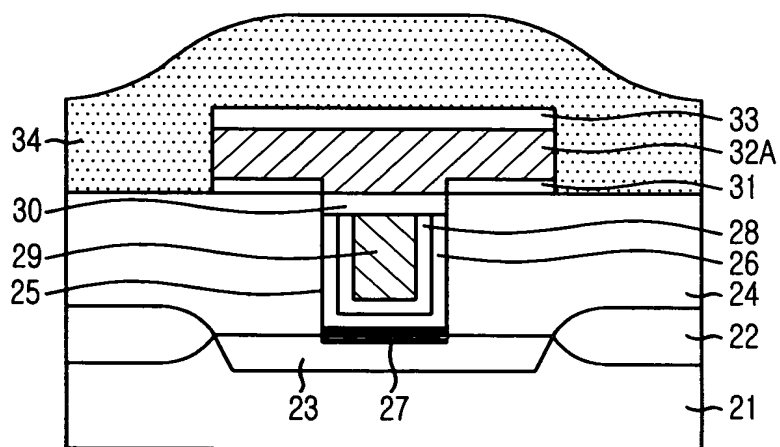
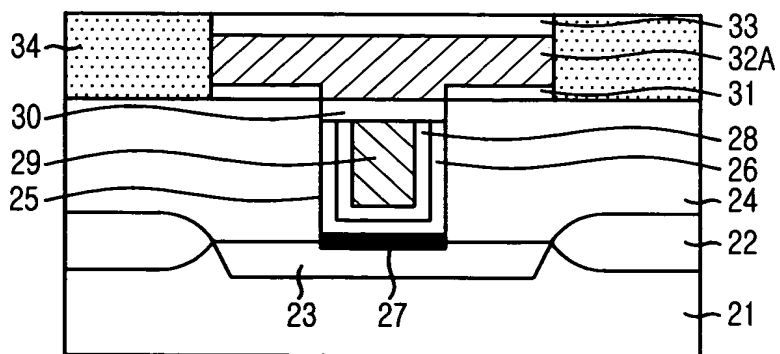


FIG. 2D



A cross-sectional view of a semiconductor device. The device features a central gate structure (23) with a gate dielectric (27) and a gate electrode (28). The gate structure is surrounded by a gate spacer (26). The device is built on a substrate (21) with a base layer (22). Above the gate structure, there are several layers: a layer (24) with a central opening, a layer (25) with a central opening, a layer (29) with a central opening, and a layer (30) with a central opening. The top surface is covered by a layer (31) with a central opening. The device is flanked by two regions (32A) with a dotted pattern, which are part of a larger structure (34) with a dotted pattern. The regions (32A) are separated by a layer (30) with a central opening.